

High-Speed Drivers with Dual SPST JFET Switches

Features

- Constant On-Resistance Over Entire Analog Range
- Low Leakage
- Low Crosstalk
- Rad Hardness

Benefits

- Low Distortion
- Eliminates Large Signal Errors
- High Precision
- High Bandwidth Capability
- Fault Protection

Applications

- Audio Switching
- Video Switching
- Sample/Hold
- Guidance and Control Systems
- Aerospace

Description

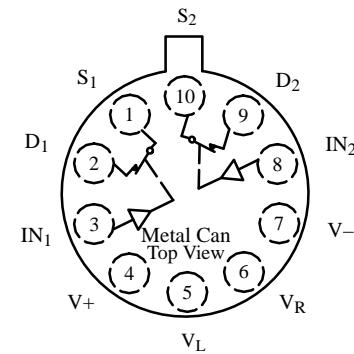
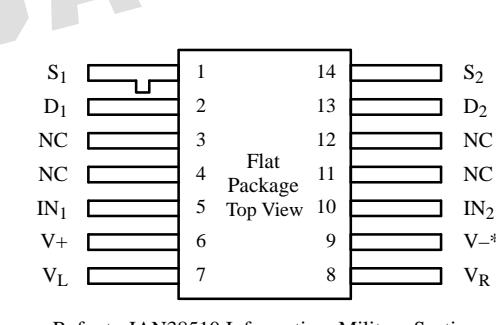
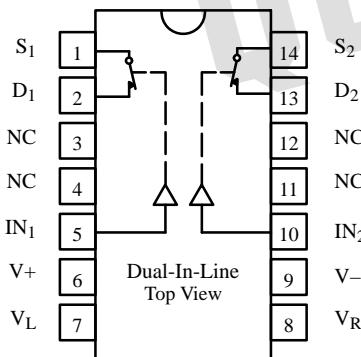
The DG180/181/182 are precision dual single-pole, single-throw (SPST) analog switches designed to provide accurate switching of video and audio signals. This series is ideally suited for applications requiring a constant on-resistance over the entire analog range.

The major difference in the devices is the on-resistance (DG180— $10\ \Omega$, DG181— $30\ \Omega$, DG182— $75\ \Omega$). Reduced errors are achieved through low leakage current ($I_{D(on)} < 2\ nA$). Applications which benefit from the flat

JFET on-resistance include audio switching, video switching, and data acquisition.

To achieve fast and accurate switch performance, each device comprises four n-channel JFET transistors and a TTL compatible bipolar driver. In the on state, each switch conducts current equally well in either direction. In the off condition, the switches will block up to 20 V peak-to-peak, with feedthrough of less than $-60\ dB$ at 10 MHz.

Functional Block Diagram and Pin Configuration



Ordering Information – DG180/181/182

Temp Range	Package	Part Number
-25 to 85°C	10-Pin Metal Can	DG181BA
	14-Pin Sidebrazed	DG180BP
	10-Pin Metal Can	DG180AA/883, 5962-8767301IA
		DG181AA/883, JM38510/11101BIA
		DG182AA/883, JM38510/11102BIA
	14-Pin Sidebrazed	DG180AP/883, 5962-8767301CA
		DG181AP/883, JM38510/11101BCA
		DG182AP/883, JM38510/11102BCA
	14-Pin Flat Pack	5962-8767301XA
		JM38510/11101BXA
		JM38510/11102BXA

*Common to Substrate and Case

Truth Table

Logic	Switch
0	ON
1	OFF

Logic "0" $\leq 0.8\ V$
Logic "1" $\geq 2.0\ V$

Switches Shown for Logic "0" Input

DG180/181/182

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Absolute Maximum Ratings

V ₊ to V ₋	36 V	Current (S or D) DG181, DG182	30 mA
V ₊ to V _D	33 V	Current (All Other Pins)	30 mA
V _D to V ₋	33 V	Storage Temperature	-65 to 150°C
V _D to V _D	±22 V	Power Dissipation ^a	
V _L to V ₋	36 V	10-Pin Metal Can ^b	450 mW
V _L to V _{IN}	8 V	14-Pin Sidebraze ^c	825 mW
V _L to V _R	8 V	14-Pin Flat Pack ^d	900 mW
V _{IN} to V _R	8 V		
V _R to V ₋	27 V		
V _R to V _{IN}	2 V		
Current (S or D) DG180	200 mA		

Notes:

- a. All leads welded or soldered to PC Board.
- b. Derate 6 mW/°C above 75°C
- c. Derate 11 mW/°C above 75°C
- d. Derate 10 mW/°C above 75°C

Specifications^a for DG180

Parameter	Symbol	Test Conditions Unless Otherwise Specified V ₊ = 15 V, V ₋ = -15 V, V _L = 5 V V _R = 0 V, V _{IN} = 2 V, 0.8 V ^f	Temp ^b	Typ ^c	A Suffix -55 to 125°C		B Suffix -25 to 85°C		Unit
					Min ^d	Max ^d	Min ^d	Max ^d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		-7.5	15	-7.5	15	V
Drain-Source On-Resistance	r _{DS(on)}	I _S = -10 mA, V _D = -7.5 V	Room Full	7.5		10 20		15 25	Ω
Source Off Leakage Current	I _{S(off)}	V _S = ± 10 V, V _D = ± 10 V V ₊ = 10 V, V ₋ = -20 V	Room Hot	0.05		10 1000		15 300	nA
		V _S = ± 7.5 V, V _D = ± 7.5 V	Room Hot	0.05		10 1000		15 300	
Drain Off Leakage Current	I _{D(off)}	V _S = ± 10 V, V _D = ± 10 V V ₊ = 10 V, V ₋ = -20 V	Room Hot	0.04		10 1000		15 300	
		V _S = ± 7.5 V, V _D = ± 7.5 V	Room Hot	0.03		10 1000		15 300	
Channel On Leakage Current	I _{D(on)}	V _D = V _S = ± 7.5 V	Room Hot	-0.1 -2 -200			-10 -200		
Saturation Drain Current	I _{DSS}	2 ms Pulse Duration	Room	300					mA
Digital Input									
Input Current with Input Voltage High	I _{INH}	V _{IN} = 5 V	Room Hot	<0.01		10 20		10 20	µA
Input Current with Input Voltage Low	I _{INL}	V _{IN} = 0 V	Full	-30	-250		-250		
Dynamic Characteristics									
Turn-On Time	t _{on}	See Switching Time Test Circuit	Room	240		400		600	ns
Turn-Off Time	t _{off}		Room	140		200		250	
Source-Off Capacitance	C _{S(off)}	f = 1 MHz	V _S = -5 V, I _D = 0	Room	21				pF
Drain-Off Capacitance	C _{D(off)}		V _D = -5 V, I _S = 0	Room	17				
Channel-On Capacitance	C _{D(on)}		V _D = V _S = 0 V	Room	17				
Off Isolation	OIRR	f = 1 MHz, R _L = 75 Ω	Room	>55					dB

Specifications^a for DG180

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15 \text{ V}$, $V_- = -15 \text{ V}$, $V_L = 5 \text{ V}$ $V_R = 0 \text{ V}$, $V_{IN} = 2 \text{ V}, 0.8 \text{ V}^f$	Temp ^b	Typ ^c	A Suffix -55 to 125°C		B Suffix -25 to 85°C		Unit
					Min ^d	Max ^d	Min ^d	Max ^d	
Power Supplies									
Positive Supply Current	I ₊	$V_{IN} = 0 \text{ V}$, or 5 V	Room	0.6		1.5		1.5	mA
Negative Supply Current	I ₋		Room	-2.7	-5		-5		
Logic Supply Current	I _L		Room	3		4.5		4.5	
Reference Supply Current	I _R		Room	-1	-2		-2		

Specifications^a for DG181

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15 \text{ V}$, $V_- = -15 \text{ V}$, $V_L = 5 \text{ V}$ $V_R = 0 \text{ V}$, $V_{IN} = 2 \text{ V}, 0.8 \text{ V}^f$	Temp ^b	Typ ^c	A Suffix -55 to 125°C		B Suffix -25 to 85°C		Unit
					Min ^d	Max ^d	Min ^d	Max ^d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		-7.5	15	-7.5	15	V
Drain-Source On-Resistance	r _{D(on)}	I _S = -10 mA, V _D = -7.5 V	Room Full	18		30 60		50 75	Ω
Source Off Leakage Current	I _{S(off)}	V _S = ± 10 V, V _D = ± 10 V V ₊ = 10 V, V ₋ = -20 V	Room Hot	0.05		1 100		5 100	nA
		V _S = ± 7.5 V, V _D = ± 7.5 V	Room Hot	0.07		1 100		5 100	
Drain Off Leakage Current	I _{D(off)}	V _S = ± 10 V, V _D = ± 10 V V ₊ = 10 V, V ₋ = -20 V	Room Hot	0.5		1 100		5 100	
		V _S = ± 7.5 V, V _D = ± 7.5 V	Room Hot	0.6		1 100		5 100	
Channel On Leakage Current	I _{D(on)}	V _D = V _S = ± 7.5 V	Room Hot	-0.02	-2 -200		-10 -200		
Digital Input									
Input Current with Input Voltage High	I _{INH}	V _{IN} = 5 V	Room Hot	<0.01		10 20		10 20	μA
Input Current with Input Voltage Low	I _{INL}	V _{IN} = 0 V	Full	-30	-250		-250		
Dynamic Characteristics									
Turn-On Time	t _{on}	See Switching Time Test Circuit	Room	85		150		180	ns
Turn-Off Time	t _{off}		Room	95		130		150	
Source-Off Capacitance	C _{S(off)}	f = 1 MHz	V _S = -5 V, I _D = 0	Room	9				pF
Drain-Off Capacitance	C _{D(off)}		V _D = -5 V, I _S = 0	Room	6				
Channel-On Capacitance	C _{D(on)}		V _D = V _S = 0 V	Room	14				
Off Isolation	OIRR	f = 1 MHz, R _L = 75 Ω	Room	>50					dB

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Specifications^a for DG181

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15 \text{ V}$, $V_- = -15 \text{ V}$, $V_L = 5 \text{ V}$ $V_R = 0 \text{ V}$, $V_{IN} = 2 \text{ V}$, 0.8 V^f	Temp ^b	Typ ^c	A Suffix -55 to 125°C		B Suffix -25 to 85°C		Unit
					Min ^d	Max ^d	Min ^d	Max ^d	
Power Supplies									
Positive Supply Current	I ₊	V _{IN} = 0 V, or 5 V	Room	0.6		1.5		1.5	mA
Negative Supply Current	I ₋		Room	-2.7	-5		-5		
Logic Supply Current	I _L		Room	3.1		4.5		4.5	
Reference Supply Current	I _R		Room	-1	-2		-2		

Specifications^a for DG182

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15 \text{ V}$, $V_- = -15 \text{ V}$, $V_L = 5 \text{ V}$ $V_R = 0 \text{ V}$, $V_{IN} = 2 \text{ V}$, 0.8 V^f	Temp ^b	Typ ^c	A Suffix -55 to 125°C		B Suffix -25 to 85°C		Unit
					Min ^d	Max ^d	Min ^d	Max ^d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		-10	15	-10	15	V
Drain-Source On-Resistance	r _{DS(on)}	I _S = -10 mA, V _D = -7.5 V	Room Full	35		75 150		100 150	Ω
Source Off Leakage Current	I _{S(off)}	V _S = ± 10 V, V _D = ± 10 V V ₊ = 10 V, V ₋ = -20 V	Room Hot	0.05		1 100		5 100	nA
		V _S = ± 10 V, V _D = ± 10 V	Room Hot	0.07		1 100		5 100	
Drain Off Leakage Current	I _{D(off)}	V _S = ± 10 V, V _D = ± 10 V V ₊ = 10 V, V ₋ = -20 V	Room Hot	0.4		1 100		5 100	
		V _S = ± 10 V, V _D = ± 10 V	Room Hot	0.5		1 100		5 100	
Channel On Leakage Current	I _{D(on)}	V _D = V _S = ± 10 V	Room Hot	-0.02	-2 -200		-10 -200		
Digital Input									
Input Current with Input Voltage High	I _{INH}	V _{IN} = 5 V	Room Hot	<0.01		10 20		10 20	μA
Input Current with Input Voltage Low	I _{INL}	V _{IN} = 0 V	Full	-30	-250		-250		
Dynamic Characteristics									
Turn-On Time	t _{on}	See Switching Time Test Circuit	Room	120		250		300	ns
Turn-Off Time	t _{off}		Room	100		130		150	
Source-Off Capacitance	C _{S(off)}	f = 1 MHz	V _S = -5 V, I _D = 0	Room	9				pF
Drain-Off Capacitance	C _{D(off)}		V _D = -5 V, I _S = 0	Room	6				
Channel-On Capacitance	C _{D(on)}		V _D = V _S = 0 V	Room	14				
Off Isolation	OIRR	f = 1 MHz, R _L = 75 Ω	Room	>50					dB

Specifications^a for DG182

Parameter	Symbol	Test Conditions Unless Otherwise Specified		Temp ^b	Typ ^c	A Suffix -55 to 125°C		B Suffix -25 to 85°C		Unit
		V ₊ = 15 V, V ₋ = -15 V, V _L = 5 V V _R = 0 V, V _{IN} = 2 V, 0.8 V ^f	Min ^d			Min ^d	Max ^d	Min ^d	Max ^d	
Power Supplies										
Positive Supply Current	I ₊	V _{IN} = 0 V, or 5 V	Room	0.6		1.5		1.5		mA
Negative Supply Current	I ₋		Room	-2.7	-5		-5			
Logic Supply Current	I _L		Room	3.1		4.5			4.5	
Reference Supply Current	I _R		Room	-1	-2		-2			

Notes:

- a. Refer to PROCESS OPTION FLOWCHART (Section 5 of the 1994 Data Book or FaxBack number 7103).
- b. Room = 25°C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

Schematic Diagram (Typical Channel)

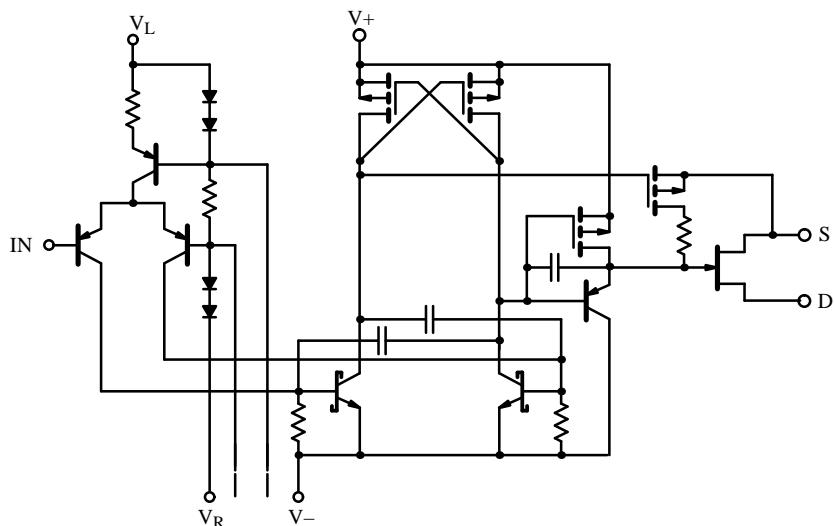


Figure 1.

DG180/181/182

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Test Circuits

Feedthrough due to charge injection may result in spikes at the leading and trailing edge of the output waveform.

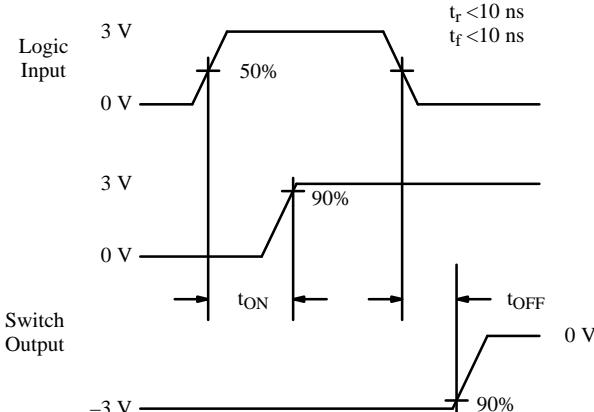
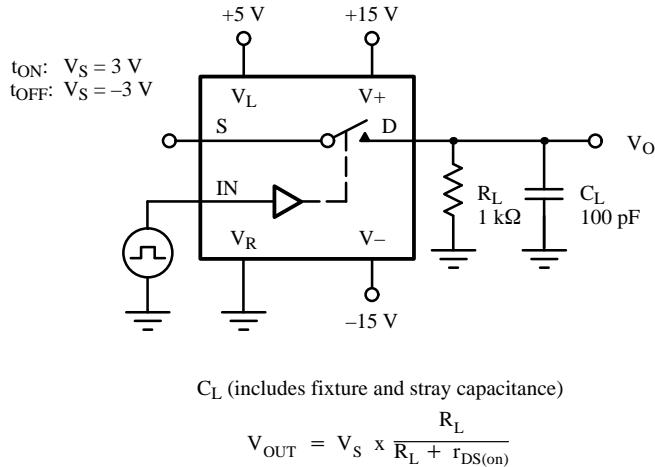


Figure 2. Switching Time

Application Hints^a

Switch	V ₊ Positive Supply Voltage (V)	V ₋ Negative Supply Voltage (V)	V _L Logic Supply Voltage (V)	V _R Reference Supply Voltage (V)	V _{IN} Logic Input Voltage V _{INH(min)} / V _{INL(max)} (V)	V _S Analog Voltage Range (V)
DG180 DG181	15 ^b	-15	5	GND	2.0/0.8	-7.5 to 15
	10	-20	5	GND	2.0/0.8	-12.5 to 10
	12	-12	5	GND	2.0/0.8	-4.5 to 12
DG182	15 ^b	-15	5	GND	2.0/0.8	-10 to 15
	10	-20	5	GND	2.0/0.8	-15 to 10
	12	-12	5	GND	2.0/0.8	-7 to 12

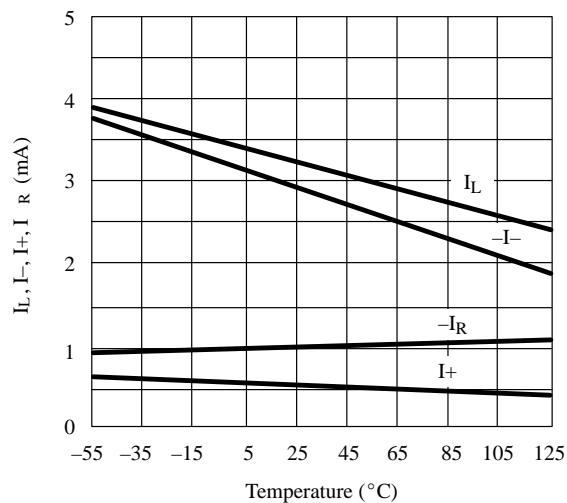
Notes:

a. Application Hints are for DESIGN AID ONLY, not guaranteed and not subject to production testing.

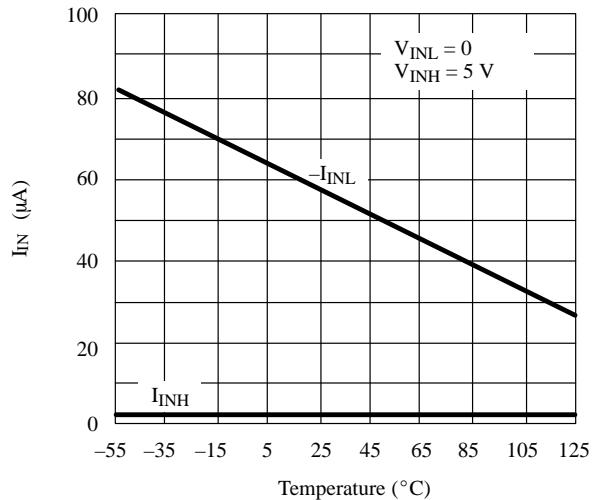
b. Electrical Parameter Chart based on V₊ = 15 V, V_L = 5 V, V_R = GND

Typical Characteristics

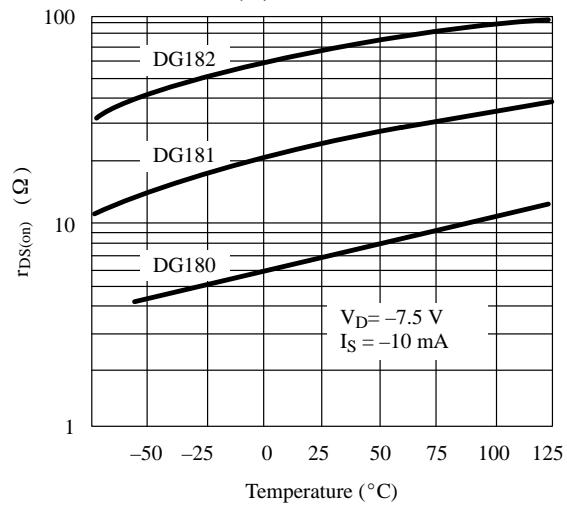
Supply Current vs. Temperature



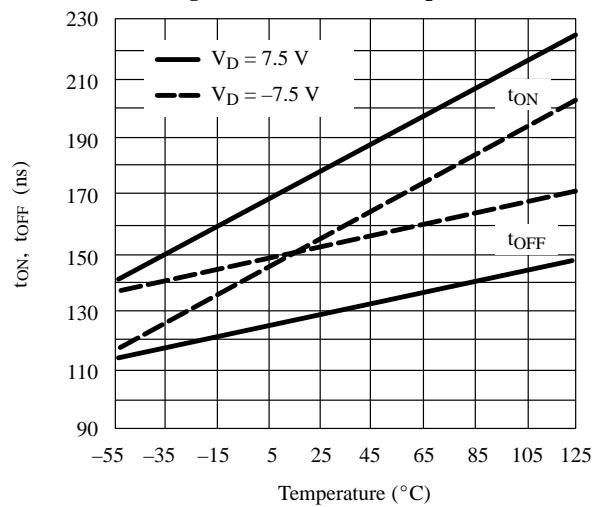
I_{IN} vs. V_{IN} and Temperature



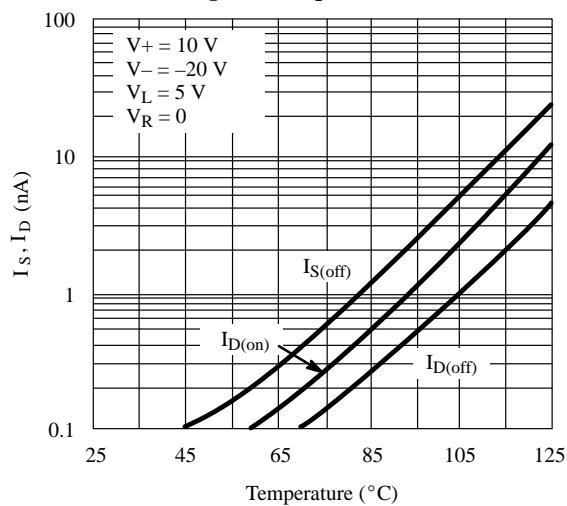
$r_{DS(on)}$ vs. Temperature



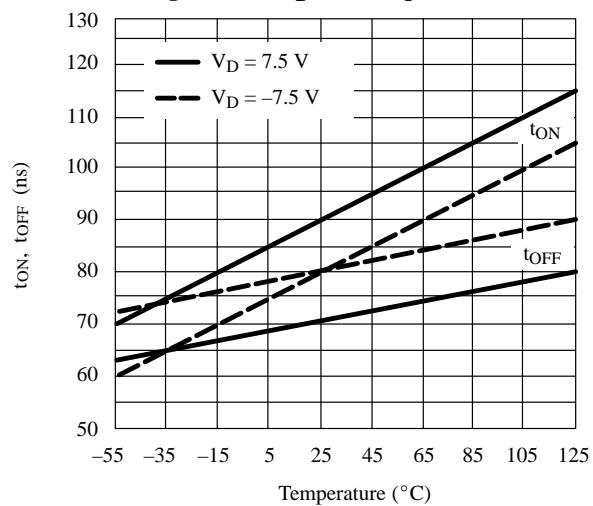
Switching Time vs. V_D and Temperature (DG180)



Leakage vs. Temperature (DG180)



Switching Time vs. V_D and Temperature (DG181/182)



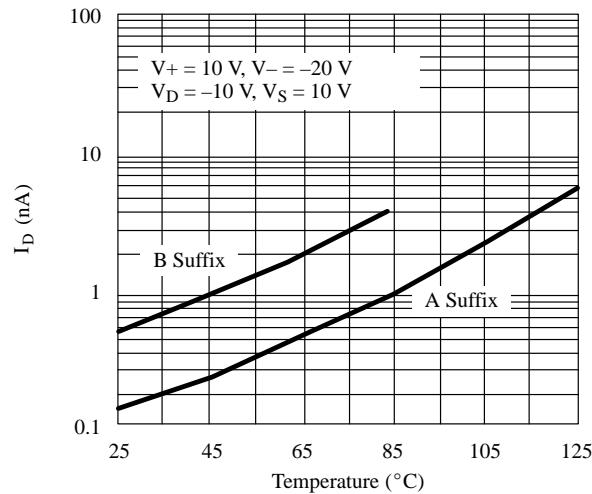
DG180/181/182

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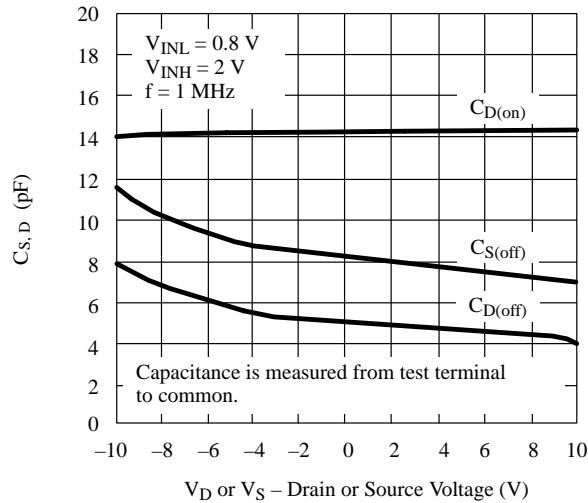
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Typical Characteristics (Cont'd)

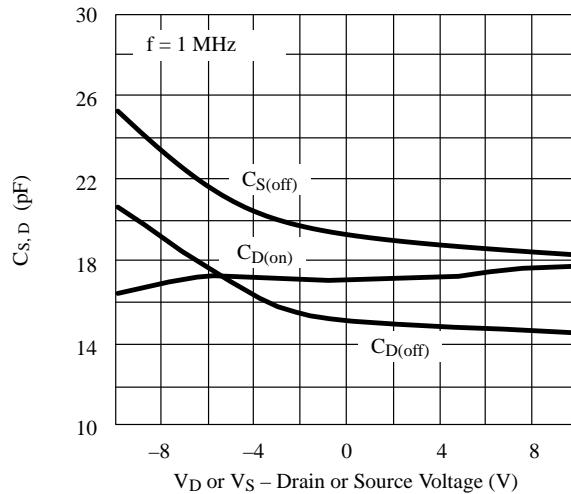
I_{D(off)} vs. Temperature (DG181/182)



Capacitance vs. V_D or V_S (DG181/182)



Capacitance vs. V_D or V_S (DG180)



Off Isolation vs. Frequency

